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Applications of "<u>Embedded -</u> <u>Microcontrollers</u>"

Details

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M3
Core Size	32-Bit Single-Core
Speed	72MHz
Connectivity	CANbus, I ² C, IrDA, LINbus, SPI, UART/USART, USB OTG
Peripherals	DMA, POR, PWM, Voltage Detect, WDT
Number of I/O	51
Program Memory Size	64KB (64K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	64K x 8
Voltage - Supply (Vcc/Vdd)	2V ~ 3.6V
Data Converters	A/D 16x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	64-LQFP
Supplier Device Package	-
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32f105r8t7

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

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1 Introduction

This datasheet provides the description of the STM32F105xx and STM32F107xx connectivity line microcontrollers. For more details on the whole STMicroelectronics STM32F10xxx family, refer to *Section 2.2: Full compatibility throughout the family*.

The STM32F105xx and STM32F107xx datasheet should be read in conjunction with the STM32F10xxx reference manual.

For information on programming, erasing and protection of the internal Flash memory refer to the STM32F10xxx Flash programming manual.

The reference and Flash programming manuals are both available from the STMicroelectronics website *www.st.com*.

For information on the Cortex[®]-M3 core refer to the Cortex[®]-M3 Technical Reference Manual, available from the www.arm.com website.





2 Description

The STM32F105xx and STM32F107xx connectivity line family incorporates the highperformance ARM[®] Cortex[®]-M3 32-bit RISC core operating at a 72 MHz frequency, highspeed embedded memories (Flash memory up to 256 Kbytes and SRAM 64 Kbytes), and an extensive range of enhanced I/Os and peripherals connected to two APB buses. All devices offer two 12-bit ADCs, four general-purpose 16-bit timers plus a PWM timer, as well as standard and advanced communication interfaces: up to two I²Cs, three SPIs, two I2Ss, five USARTs, an USB OTG FS and two CANs. Ethernet is available on the STM32F107xx only.

The STM32F105xx and STM32F107xx connectivity line family operates in the –40 to +105 °C temperature range, from a 2.0 to 3.6 V power supply. A comprehensive set of power-saving mode allows the design of low-power applications.

The STM32F105xx and STM32F107xx connectivity line family offers devices in three different package types: from 64 pins to 100 pins. Depending on the device chosen, different sets of peripherals are included, the description below gives an overview of the complete range of peripherals proposed in this family.

These features make the STM32F105xx and STM32F107xx connectivity line microcontroller family suitable for a wide range of applications such as motor drives and application control, medical and handheld equipment, industrial applications, PLCs, inverters, printers, and scanners, alarm systems, video intercom, HVAC and home audio equipment.

2.1 Device overview

Figure 1 shows the general block diagram of the device family.

Peripherals ⁽¹⁾		ST	STM32F105Rx			STM32F107Rx		STM32F105Vx			STM32F107Vx	
Flash men	64	128	256	128	256	64	128	256	128	256		
SRAM in K	Kbytes						64			1		
Package				LQFP6	64		LQFP 100	LQFP 100, BGA 100	LQFP 100	,		
Ethernet			No		Y	es		No		Yes		
	General- purpose						4			<u>.</u>		
Timers	Advanced- control	1										
	Basic						2					

Tabla 2	STM32E105vv a	nd STM32E107vv	fostures and	peripheral counts	
Table 2.	31 WJ32F 103XX a	11U ST W32F 107 XX	leatures and	periprieral counts	



Any of the standard timers can be used to generate PWM outputs. Each of the timers has independent DMA request generations.

Basic timers TIM6 and TIM7

These timers are mainly used for DAC trigger generation. They can also be used as a generic 16-bit time base.

Independent watchdog

The independent watchdog is based on a 12-bit downcounter and 8-bit prescaler. It is clocked from an independent 40 kHz internal RC and as it operates independently from the main clock, it can operate in Stop and Standby modes. It can be used either as a watchdog to reset the device when a problem occurs, or as a free running timer for application timeout management. It is hardware or software configurable through the option bytes. The counter can be frozen in debug mode.

Window watchdog

The window watchdog is based on a 7-bit downcounter that can be set as free running. It can be used as a watchdog to reset the device when a problem occurs. It is clocked from the main clock. It has an early warning interrupt capability and the counter can be frozen in debug mode.

SysTick timer

This timer is dedicated to real-time operating systems, but could also be used as a standard down counter. It features:

- A 24-bit down counter
- Autoreload capability
- Maskable system interrupt generation when the counter reaches 0.
- Programmable clock source

2.3.16 I²C bus

Up to two I²C bus interfaces can operate in multimaster and slave modes. They can support standard and fast modes.

They support 7/10-bit addressing mode and 7-bit dual addressing mode (as slave). A hardware CRC generation/verification is embedded.

They can be served by DMA and they support SMBus 2.0/PMBus.

2.3.17 Universal synchronous/asynchronous receiver transmitters (USARTs)

The STM32F105xx and STM32F107xx connectivity line embeds three universal synchronous/asynchronous receiver transmitters (USART1, USART2 and USART3) and two universal asynchronous receiver transmitters (UART4 and UART5).

These five interfaces provide asynchronous communication, IrDA SIR ENDEC support, multiprocessor communication mode, single-wire half-duplex communication mode and have LIN Master/Slave capability.

The USART1 interface is able to communicate at speeds of up to 4.5 Mbit/s. The other available interfaces communicate at up to 2.25 Mbit/s.



- 32-bit CRC generation and removal
- Several address filtering modes for physical and multicast address (multicast and group addresses)
- 32-bit status code for each transmitted or received frame
- Internal FIFOs to buffer transmit and receive frames. The transmit FIFO and the receive FIFO are both 2 Kbytes, that is 4 Kbytes in total
- Supports hardware PTP (precision time protocol) in accordance with IEEE 1588 with the timestamp comparator connected to the TIM2 trigger input
- Triggers interrupt when system time becomes greater than target time

2.3.21 Controller area network (CAN)

The two CANs are compliant with the 2.0A and B (active) specifications with a bitrate up to 1 Mbit/s. They can receive and transmit standard frames with 11-bit identifiers as well as extended frames with 29-bit identifiers. Each CAN has three transmit mailboxes, two receive FIFOS with 3 stages and 28 shared scalable filter banks (all of them can be used even if one CAN is used). The 256 bytes of SRAM which are allocated for each CAN (512 bytes in total) are not shared with any other peripheral.

2.3.22 Universal serial bus on-the-go full-speed (USB OTG FS)

The STM32F105xx and STM32F107xx connectivity line devices embed a USB OTG fullspeed (12 Mb/s) device/host/OTG peripheral with integrated transceivers. The USB OTG FS peripheral is compliant with the USB 2.0 specification and with the OTG 1.0 specification. It has software-configurable endpoint setting and supports suspend/resume. The USB OTG full-speed controller requires a dedicated 48 MHz clock that is generated by a PLL connected to the HSE oscillator. The major features are:

- 1.25 KB of SRAM used exclusively by the endpoints (not shared with any other peripheral)
- 4 bidirectional endpoints
- HNP/SNP/IP inside (no need for any external resistor)
- for OTG/Host modes, a power switch is needed in case bus-powered devices are connected
- the SOF output can be used to synchronize the external audio DAC clock in isochronous mode
- in accordance with the USB 2.0 Specification, the supported transfer speeds are:
 - in Host mode: full speed and low speed
 - in Device mode: full speed

2.3.23 GPIOs (general-purpose inputs/outputs)

Each of the GPIO pins can be configured by software as output (push-pull or open-drain), as input (with or without pull-up or pull-down) or as peripheral alternate function. Most of the GPIO pins are shared with digital or analog alternate functions. All GPIOs are high current-capable.

The I/Os alternate function configuration can be locked if needed following a specific sequence in order to avoid spurious writing to the I/Os registers.

I/Os on APB2 with up to 18 MHz toggling speed



Eight DAC trigger inputs are used in the STM32F105xx and STM32F107xx connectivity line family. The DAC channels are triggered through the timer update outputs that are also connected to different DMA channels.

2.3.27 Temperature sensor

The temperature sensor has to generate a voltage that varies linearly with temperature. The conversion range is between 2 V < V_{DDA} < 3.6 V. The temperature sensor is internally connected to the ADC1_IN16 input channel which is used to convert the sensor output voltage into a digital value.

2.3.28 Serial wire JTAG debug port (SWJ-DP)

The ARM SWJ-DP Interface is embedded, and is a combined JTAG and serial wire debug port that enables either a serial wire debug or a JTAG probe to be connected to the target. The JTAG TMS and TCK pins are shared respectively with SWDIO and SWCLK and a specific sequence on the TMS pin is used to switch between JTAG-DP and SW-DP.

2.3.29 Embedded Trace Macrocell™

The ARM[®] Embedded Trace Macrocell provides a greater visibility of the instruction and data flow inside the CPU core by streaming compressed data at a very high rate from the STM32F10xxx through a small number of ETM pins to an external hardware trace port analyzer (TPA) device. The TPA is connected to a host computer using USB, Ethernet, or any other high-speed channel. Real-time instruction and data flow activity can be recorded and then formatted for display on the host computer running debugger software. TPA hardware is commercially available from common development tool vendors. It operates with third party debugger software tools.



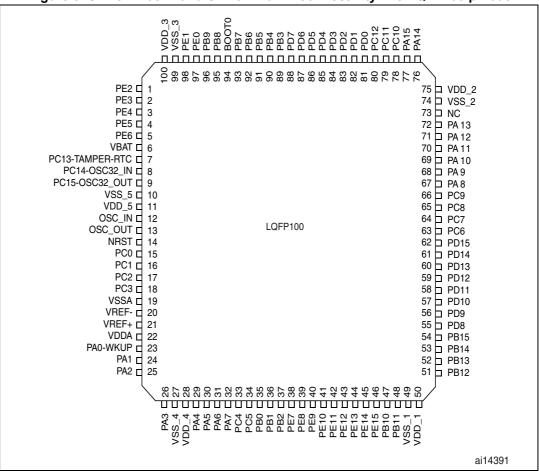






Table	5.	Pin	definitions	
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	Pins						Alternate func	tions ⁽⁴⁾
BGA100	LQFP64	LQFP100	Pin name	Type ⁽¹⁾	I / O Level ⁽²⁾	Main function ⁽³⁾ (after reset)	Default	Remap
A3	-	1	PE2	I/O	FT	PE2	TRACECK	-
B3	-	2	PE3	I/O	FT	PE3	TRACED0	-
C3	-	3	PE4	I/O	FT	PE4	TRACED1	-
D3	-	4	PE5	I/O	FT	PE5	TRACED2	-
E3	-	5	PE6	I/O	FT	PE6	TRACED3	-
B2	1	6	V _{BAT}	S	-	V _{BAT}	-	-
A2	2	7	PC13-TAMPER- RTC ⁽⁵⁾	I/O	-	PC13 ⁽⁶⁾	TAMPER-RTC	-
A1	3	8	PC14- OSC32_IN ⁽⁵⁾	I/O	-	PC14 ⁽⁶⁾	OSC32_IN	-
B1	4	9	PC15- OSC32_OUT ⁽⁵⁾	I/O	-	PC15 ⁽⁶⁾	OSC32_OUT	-
C2	-	10	V _{SS_5}	S	-	V _{SS_5}	-	-
D2	-	11	V _{DD_5}	S	-	V _{DD_5}	-	-
C1	5	12	OSC_IN	Ι	-	OSC_IN	-	-
D1	6	13	OSC_OUT	0	-	OSC_OUT	-	-
E1	7	14	NRST	I/O	-	NRST	-	-
F1	8	15	PC0	I/O	-	PC0	ADC12_IN10	-
F2	9	16	PC1	I/O	-	PC1	ADC12_IN11/ ETH_MII_MDC/ ETH_RMII_MDC	-
E2	10	17	PC2	I/O	-	PC2	ADC12_IN12/ ETH_MII_TXD2	-
F3	11	18	PC3	I/O	-	PC3	ADC12_IN13/ ETH_MII_TX_CLK	-
G1	12	19	V _{SSA}	S	-	V _{SSA}	-	-
H1	-	20	V _{REF-}	S	-	V _{REF-}	-	-
J1	-	21	V _{REF+}	S	-	V _{REF+}	-	-
K1	13	22	V _{DDA}	S	-	V _{DDA}	-	-
G2	14	23	PA0-WKUP	I/O	-	PA0	WKUP/USART2_CTS ⁽⁷⁾ ADC12_IN0/TIM2_CH1_ETR TIM5_CH1/ ETH_MII_CRS_WKUP	-



5.3.2 Operating conditions at power-up / power-down

Subject to general operating conditions for T_A .

Symbol	Parameter	Condition	Min	Мах	Unit
t _{VDD}	V_{DD} rise time rate		0	-	μs/V
TJ	V _{DD} fall time rate	-	20	-	μ5/ V

Table 10. Operating condition at power-up / power down

5.3.3 Embedded reset and power control block characteristics

The parameters given in *Table 11* are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in *Table 9*.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		PLS[2:0]=000 (rising edge)	2.1	2.18	2.26	V
		PLS[2:0]=000 (falling edge)	2	2.08	2.16	V
		PLS[2:0]=001 (rising edge)	2.19	2.28	2.37	V
V _{PVD} Programmable voltage detector level selection PLS[2:0]=001 (rising edge) 2.19 2.28 PLS[2:0]=001 (falling edge) 2.09 2.18 PLS[2:0]=010 (rising edge) 2.28 2.38 PLS[2:0]=010 (rising edge) 2.18 2.28 PLS[2:0]=010 (rising edge) 2.18 2.28 PLS[2:0]=011 (rising edge) 2.38 2.48 PLS[2:0]=011 (rising edge) 2.28 2.38 PLS[2:0]=011 (rising edge) 2.28 2.38 PLS[2:0]=010 (rising edge) 2.38 2.48 PLS[2:0]=100 (rising edge) 2.47 2.58 PLS[2:0]=100 (rising edge) 2.37 2.48 PLS[2:0]=101 (rising edge) 2.57 2.68	2.27	V				
		PLS[2:0]=010 (rising edge)	2.28	2.38	2.48	V
		PLS[2:0]=010 (falling edge)	2.18	2.28	2.38	V
		PLS[2:0]=011 (rising edge)	2.38	2.48	2.58	V
V	Programmable voltage	PLS[2:0]=011 (falling edge)	2.28	2.38	2.48	V
V _{PVD} Programmable voltage PLS[2:0]=100 (rising edge) 2.4 PLS[2:0]=100 (falling edge) 2.3 PLS[2:0]=101 (rising edge) 2.5	detector level selection	PLS[2:0]=100 (rising edge)	2.47	2.58	2.69	V
		PLS[2:0]=100 (falling edge)	2.37	2.48	2.59	V
	2.57	2.68	2.79	V		
		PLS[2:0]=101 (falling edge)	2.47	2.18 2.26 V 2.08 2.16 V 2.28 2.37 V 2.18 2.27 V 2.38 2.48 V 2.38 2.69 V 2.58 2.69 V 2.78 2.9 V 2.88 3 V 2.78 2.9 V 1.00 - mV 1.88 1.96 V 1.92 2.0 V 40 - mV	V	
PLS[2:0]=101 (falling edge) 2.47 2.58 PLS[2:0]=110 (rising edge) 2.66 2.78	2.9	V				
		PLS[2:0]=110 (falling edge)	2.56	2.68	2.8	V
		PLS[2:0]=111 (rising edge)	2.76	7 2.58 2.69 V 6 2.78 2.9 V 6 2.68 2.8 V 6 2.88 3 V	V	
		PLS[2:0]=111 (falling edge)	2.66	2.78	2.9	V
V _{PVDhyst} ⁽²⁾	PVD hysteresis	-	-	100	-	mV
M	Power on/power down	Falling edge	1.8 ⁽¹⁾	1.88	1.96	V
V _{POR/PDR}	reset threshold	Rising edge	1.84	1.92	2.0	V
V _{PDRhyst} ⁽²⁾	PDR hysteresis	-	-	40	-	mV
T _{RSTTEMPO} ⁽²⁾	Reset temporization	-	1	2.5	4.5	ms

Table 11. Embedded reset and power control block characteristics

1. The product behavior is guaranteed by design down to the minimum $V_{\mbox{POR/PDR}}$ value.

2. Guaranteed by design, not tested in production.



				Туј	0 ⁽¹⁾	
Symbol	Parameter	Conditions	f _{HCLK}	All peripherals enabled ⁽²⁾	All peripherals disabled	Unit
			72 MHz	28.2	6	
			48 MHz	19	4.2	
			36 MHz	14.7	3.4	
			24 MHz	10.1	2.5	
			16 MHz	6.7	2	
		External clock ⁽³⁾	8 MHz	3.2	1.3	
			4 MHz	2.3	1.2	
			2 MHz	1.7	1.16	mA
			1 MHz	1.5	1.1	
I.	Supply current in		500 kHz	1.3	1.05	
I _{DD}	Sleep mode		125 kHz	1.2	1.05	ШA
			36 MHz	13.7	2.6	
			24 MHz	9.3	1.8	
			16 MHz	6.3	1.3	
		Running on high speed internal RC	8 MHz	2.7	0.6	
		(HSI), AHB prescaler	4 MHz	1.6	0.5	
		used to reduce the frequency	2 MHz	1	0.46	
		1	1 MHz	0.8	0.44	
			500 kHz	0.6	0.43	
			125 kHz	0.5	0.42	

Table 18. Typical current consumption in Sleep mode, code running from Flash or RAM

1. Typical values are measures at $T_A = 25$ °C, $V_{DD} = 3.3$ V.

2. Add an additional power consumption of 0.8 mA per ADC for the analog part. In applications, this consumption occurs only while the ADC is on (ADON bit is set in the ADC_CR2 register).

3. External clock is 8 MHz and PLL is on when f_{HCLK} > 8 MHz.

On-chip peripheral current consumption

The current consumption of the on-chip peripherals is given in *Table 19*. The MCU is placed under the following conditions:

- all I/O pins are in input mode with a static value at V_{DD} or V_{SS} (no load)
- all peripherals are disabled unless otherwise mentioned
- the given value is calculated by measuring the current consumption
 - with all peripherals clocked off
 - with one peripheral clocked on (with only the clock applied)
- ambient operating temperature and V_{DD} supply voltage conditions summarized in Table 6



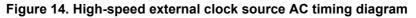
Low-speed external user clock generated from an external source

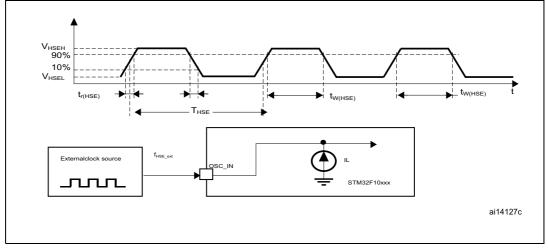
The characteristics given in *Table 21* result from tests performed using an low-speed external clock source, and under ambient temperature and supply voltage conditions summarized in *Table 9*.

			· · · · · · · · · · · · · · · · · · ·								
Symbol	Parameter	Conditions	Min	Тур	Мах	Unit					
f _{LSE_ext}	User External clock source frequency ⁽¹⁾			32.768	1000	kHz					
V _{LSEH}	OSC32_IN input pin high level voltage		0.7V _{DD}	-	V _{DD}	V					
V _{LSEL}	OSC32_IN input pin low level voltage	-	V _{SS}	-	0.3V _{DD}	v					
t _{w(LSE)} t _{w(LSE)}	OSC32_IN high or low time ⁽¹⁾		450	-	-	ns					
t _{r(LSE)} t _{f(LSE)}	OSC32_IN rise or fall time ⁽¹⁾		-	-	50	19					
C _{in(LSE)}	OSC32_IN input capacitance ⁽¹⁾	-	-	5		pF					
DuCy _(LSE)	Duty cycle	-	30	-	70	%					
١ _L	OSC32_IN Input leakage current	$V_{SS} \leq V_{IN} \leq V_{DD}$	-	-	±1	μA					

Table 21. Low-speed external user clock characteristics

1. Guaranteed by design, not tested in production.







Symbol	Parameter	Cond	litions	Min	Тур	Max	Unit
		T _A = 50 °C	-	1.5	-		
		T _A = 25 °C	-	2.5	-		
		T _A = 10 °C	-	4	-		
t _{SU(LSE)}	t _{SU(LSE)} Startup time		T _A = 0 °C	-	6	-	
(4)	Startup time	V_{DD} is stabilized	T _A = -10 °C	-	10	-	S
			T _A = -20 °C	-	17	-	
			T _A = -30 °C	-	32	-	
			T _A = -40 °C	-	60	-	

Table 23. LSE oscillator characteristics (f_{LSE} = 32.768 kHz) ⁽¹⁾ (continued)

1. Based on characterization, not tested in production.

2. Refer to the note and caution paragraphs below the table, and to the application note AN2867 "Oscillator design guide for ST microcontrollers".

3. The oscillator selection can be optimized in terms of supply current using an high quality resonator with small R_S value for example MSIV-TIN32.768kHz. Refer to crystal manufacturer for more details

- 4. t_{SU(LSE)} is the startup time measured from the moment it is enabled (by software) to a stabilized 32.768 kHz oscillation is reached. This value is measured for a standard crystal and it can vary significantly with the crystal manufacturer
- Note: For C_{L1} and C_{L2} it is recommended to use high-quality external ceramic capacitors in the 5 pF to 15 pF range selected to match the requirements of the crystal or resonator (see Figure 17). C_{L1} and C_{L2} , are usually the same size. The crystal manufacturer typically specifies a load capacitance which is the series combination of C_{L1} and C_{L2} . Load capacitance C_L has the following formula: $C_L = C_{L1} \times C_{L2} / (C_{L1} + C_{L2}) + C_{stray}$ where C_{stray} is the pin capacitance and board or trace PCB-related capacitance. Typically, it is between 2 pF and 7 pF.
- **Caution:** To avoid exceeding the maximum value of C_{L1} and C_{L2} (15 pF) it is strongly recommended to use a resonator with a load capacitance $C_L \le 7$ pF. Never use a resonator with a load capacitance of 12.5 pF.

Example: if you choose a resonator with a load capacitance of $C_L = 6 \text{ pF}$, and $C_{stray} = 2 \text{ pF}$, then $C_{L1} = C_{L2} = 8 \text{ pF}$.

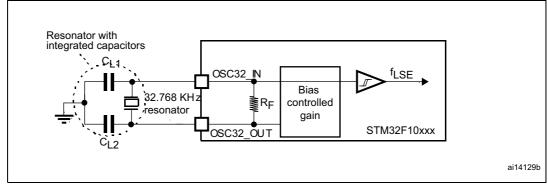


Figure 17. Typical application with a 32.768 kHz crystal



5.3.7 Internal clock source characteristics

The parameters given in *Table 24* are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in *Table 9*.

High-speed internal (HSI) RC oscillator

Parameter	Conditions		Min	Тур	Max	Unit				
Frequency		-	-	8		MHz				
Duty cycle	-		45	-	55	%				
	User-trimmed register ⁽²⁾	with the RCC_CR	-	-	1 ⁽³⁾	%				
Accuracy of the HSI oscillator	Factory- calibrated ⁽⁴⁾	$T_A = -40$ to 105 °C	-2	-	2.5	%				
		T _A = −10 to 85 °C	-1.5	-	2.2	%				
		T _A = 0 to 70 °C	-1.3	-	2	%				
		T _A = 25 °C	-1.1	-	1.8	%				
HSI oscillator startup time		-	1	-	2	μs				
HSI oscillator power consumption		-	-	80	100	μA				
	Frequency Duty cycle Accuracy of the HSI oscillator HSI oscillator startup time	Frequency Image: Constraint of the startup time Duty cycle User-trimmed register ⁽²⁾ Accuracy of the HSI oscillator Factory-calibrated ⁽⁴⁾ HSI oscillator Image: Constraint of the startup time	Frequency-Duty cycle-Accuracy of the HSI oscillatorUser-trimmed with the RCC_CR register ⁽²⁾ Factory- calibrated ⁽⁴⁾ $T_A = -40 \text{ to } 105 ^{\circ}\text{C}$ $T_A = -10 \text{ to } 85 ^{\circ}\text{C}$ $T_A = 0 \text{ to } 70 ^{\circ}\text{C}$ $T_A = 25 ^{\circ}\text{C}$ HSI oscillator startup time-	FrequencyDuty cycle-45Accuracy of the HSI oscillatorUser-trimmed with the RCC_CR register ⁽²⁾ - $Accuracy of the HSIoscillatorT_A = -40 to 105 °CT_A = -10 to 85 °CT_A = 0 to 70 °CT_A = 25 °C-2HSI oscillatorstartup time-1$	Frequency - - 8 Duty cycle - 45 - Accuracy of the HSI oscillator User-trimmed with the RCC_CR register ⁽²⁾ - - 7 Accuracy of the HSI oscillator $T_A = -40 \text{ to } 105 ^{\circ}\text{C}$ -2 - HSI oscillator startup time $T_A = 0 \text{ to } 70 ^{\circ}\text{C}$ -1.3 - HSI oscillator - - 1 -	$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$				

Table 24.	HSI oscillator	characteristics ⁽¹⁾
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1. V_{DD} = 3.3 V, T_A = -40 to 105 °C unless otherwise specified.

2. Refer to application note AN2868 "STM32F10xxx internal RC oscillator (HSI) calibration" available from the ST website *www.st.com*.

3. Guaranteed by design, not tested in production.

4. Based on characterization, not tested in production.

Low-speed internal (LSI) RC oscillator

Table 25. LSI oscillator characteristics (1)
---	---

Symbol	Parameter	Min	Тур	Мах	Unit
f _{LSI} ⁽²⁾	Frequency	30	40	60	kHz
t _{su(LSI)} ⁽³⁾	LSI oscillator startup time	-	-	85	μs
I _{DD(LSI)} ⁽³⁾	LSI oscillator power consumption	-	0.65	1.2	μA

1. V_{DD} = 3 V, T_A = -40 to 105 °C unless otherwise specified.

2. Based on characterization, not tested in production.

3. Guaranteed by design, not tested in production.

Wakeup time from low-power mode

The wakeup times given in *Table 26* is measured on a wakeup phase with a 8-MHz HSI RC oscillator. The clock source used to wake up the device depends from the current operating mode:

- Stop or Standby mode: the clock source is the RC oscillator
- Sleep mode: the clock source is the clock that was set before entering Sleep mode.



5.3.9 Memory characteristics

Flash memory

The characteristics are given at $T_A = -40$ to 105 °C unless otherwise specified.

Symbol	Parameter	Conditions	Min ⁽¹⁾	Тур	Max ⁽¹⁾	Unit
t _{prog}	16-bit programming time	T _A = -40 to +105 °C	40	52.5	70	μs
t _{ERASE}	Page (1 KB) erase time	$T_A = -40$ to +105 °C	20	-	40	ms
t _{ME}	Mass erase time	$T_A = -40$ to +105 °C	20	-	40	ms
		Read mode f _{HCLK} = 72 MHz with 2 wait states, V _{DD} = 3.3 V	-	-	20	mA
I _{DD}	Supply current	Write / Erase modes f _{HCLK} = 72 MHz, V _{DD} = 3.3 V	-	-	5	mA
		Power-down mode / Halt, V_{DD} = 3.0 to 3.6 V	-	-	50	μA
V _{prog}	Programming voltage	-	2	-	3.6	V

Table 29	. Flash	memory	characteristics
----------	---------	--------	-----------------

1. Guaranteed by design, not tested in production.

Symbol	Parameter	Conditions	Min ⁽¹⁾	Тур	Max ⁽¹⁾	Unit
N _{END}	Endurance	$T_A = -40$ to +85 °C (6 suffix versions) $T_A = -40$ to +105 °C (7 suffix versions)	10	-	-	Kcycles
		1 kcycle ⁽²⁾ at T _A = 85 °C	30	-	-	
t _{RET}	Data retention	1 kcycle ⁽²⁾ at T _A = 105 °C	10	-	-	Years
		10 kcycles ⁽²⁾ at T _A = 55 °C	20	-	-	

Table 30. Flash memory endurance and data retention

1. Based on characterization, not tested in production.

2. Cycling performed over the whole temperature range.

5.3.10 EMC characteristics

Susceptibility tests are performed on a sample basis during device characterization.

Functional EMS (electromagnetic susceptibility)

While a simple application is executed on the device (toggling 2 LEDs through I/O ports). the device is stressed by two electromagnetic events until a failure occurs. The failure is indicated by the LEDs:

- Electrostatic discharge (ESD) (positive and negative) is applied to all device pins until a functional disturbance occurs. This test is compliant with the IEC 61000-4-2 standard.
- FTB: A burst of fast transient voltage (positive and negative) is applied to V_{DD} and V_{SS} through a 100 pF capacitor, until a functional disturbance occurs. This test is compliant with the IEC 61000-4-4 standard.



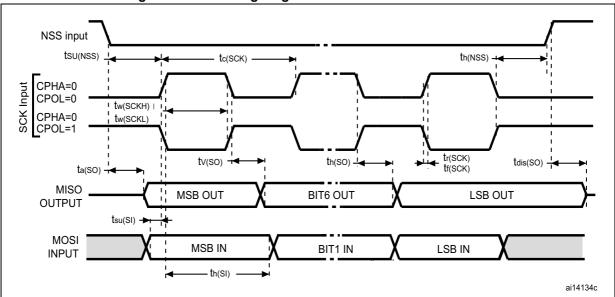
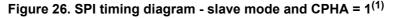
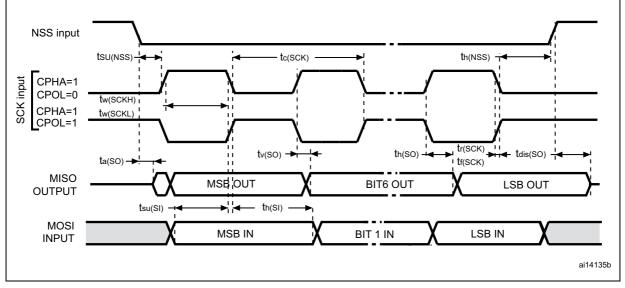


Figure 25. SPI timing diagram - slave mode and CPHA = 0





1. Measurement points are done at CMOS levels: $0.3V_{DD}$ and $0.7V_{DD}$.



Symbol	Parameter	Conditions		Min	Мах	Unit
f _{CK}	I ² S clock frequency	Master data: 16 bits, a freq = 48 K	audio	1.52	1.54	MHz
1/t _{c(CK)}		Slave		0	6.5	
t _{r(CK)} t _{f(CK)}	I ² S clock rise and fall time	capacitive load C _L = 5	50 pF	-	8	
t _{w(CKH)} ⁽¹⁾	I ² S clock high time	Master f _{PCLK} = 16 MH	łz,	317	320	
t _{w(CKL)} ⁽¹⁾	I ² S clock low time	audio freq = 48 K		333	336	
t _{v(WS)} ⁽¹⁾	WS valid time	Master mode		3	-	
t _{h(WS)} ⁽¹⁾	WS hold time	Master mode	I2S2	0	-	ns
^ι h(WS) `´		Master mode	I2S3	0	-	
+ (1)	W/S actus time	Slave mode	I2S2	4	-	
t _{su(WS)} ⁽¹⁾	WS setup time	Slave mode	I2S3	9	-	-
t _{h(WS)} ⁽¹⁾	WS hold time	Slave mode	Slave mode		-	
DuCy(SCK)	I2S slave input clock duty cycle	Slave mode	Slave mode		70	%
+ (1)		Master receiver	I2S2	8	-	
t _{su(SD_MR)} ⁽¹⁾	- Data input setup time	1283	I2S3	10	-	
t (1)		Slave receiver	I2S2	3	-	_
t _{su(SD_SR)} ⁽¹⁾		Slave receiver	I2S3	8	-	
t _{h(SD_MR)} ⁽¹⁾		Master receiver	I2S2	2	-	
^u h(SD_MR)`´	- Data input hold time	Inaster receiver	I2S3	4	-	
+ (1)		Slave receiver	I2S2	2	-	
t _{h(SD_SR)} ⁽¹⁾		Slave receiver	I2S3	4	-	
t (1)(3)	Data output valid time	Slave transmitter	I2S2	23	-	ns
t _{v(SD_ST)} (1)(3)	Data output valid time	(after enable edge)	I2S3	33	-	
+ (1) r	Data output hold time	Slave transmitter	I2S2	29	-	
$t_{h(SD_ST)}$ ⁽¹⁾		(after enable edge)	I2S3	27	-	
t (1)	Data output valid time	Master transmitter	I2S2	-	5	
$t_{v(SD_MT)}$ ⁽¹⁾		(after enable edge)	I2S3	-	2]
t (1)	Data output hold time	Master transmitter	I2S2	11	-	
t _{h(SD_MT)} ⁽¹⁾	Data output hold time	(after enable edge)	I2S3	4	-	

Table 44. I²S characteristics

1. Based on design simulation and/or characterization results, not tested in production.



Table 51. Dynamic characteristics. Ethemet MAC signals for Min						
Symbol	Rating	Min	Тур	Мах	Unit	
t _{su(RXD)}	Receive data setup time	10	-	-	ns	
t _{ih(RXD)}	Receive data hold time	10	-	-	ns	
t _{su(DV)}	Data valid setup time	10	-	-	ns	
t _{ih(DV)}	Data valid hold time	10	-	-	ns	
t _{su(ER)}	Error setup time	10	-	-	ns	
t _{ih(ER)}	Error hold time	10	-	-	ns	
t _{d(TXEN)}	Transmit enable valid delay time	14	16	18	ns	
t _{d(TXD)}	Transmit data valid delay time	13	16	20	ns	

 Table 51. Dynamic characteristics: Ethernet MAC signals for MII

CAN (controller area network) interface

Refer to Section 5.3.12: I/O current injection characteristics for more details on the input/output alternate function characteristics (CANTX and CANRX).

5.3.17 12-bit ADC characteristics

Unless otherwise specified, the parameters given in *Table 52* are derived from tests performed under the ambient temperature, f_{PCLK2} frequency and V_{DDA} supply voltage conditions summarized in *Table 9*.

Note: It is recommended to perform a calibration after each power-up.

Table 52. ADC characteristics						
Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
V_{DDA}	Power supply	-	2.4	-	3.6	V
V_{REF^+}	Positive reference voltage	-	2.4	-	V _{DDA}	V
I _{VREF}	Current on the V _{REF} input pin	-	-	160 ⁽¹⁾	220 ⁽¹⁾	μA
f _{ADC}	ADC clock frequency	-	0.6	-	14	MHz
$f_{S}^{(2)}$	Sampling rate	-	0.05	-	1	MHz
د (2)		f _{ADC} = 14 MHz	-	-	823	kHz
f _{TRIG} ⁽²⁾	External trigger frequency	-	-	-	17	1/f _{ADC}
V _{AIN}	Conversion voltage range ⁽³⁾	-	0 (V _{SSA} or V _{REF-} tied to ground)	-	V _{REF+}	V
$R_{AIN}^{(2)}$	External input impedance	See <i>Equation 1</i> and <i>Table 53</i> for details	-	-	50	kΩ
$R_{ADC}^{(2)}$	Sampling switch resistance	-	-	-	1	kΩ
$C_{ADC}^{(2)}$	Internal sample and hold capacitor	-	-	-	8	pF
+ (2)	Colibration time	f _{ADC} = 14 MHz	5	.9		μs
t _{CAL} ⁽²⁾	Calibration time	-	83			1/f _{ADC}



Device marking for LQFP64

The following figure shows the device marking for the LQFP64 package.

Other optional marking or inset/upset marks, which identify the parts throughout supply chain operations, are not indicated below.

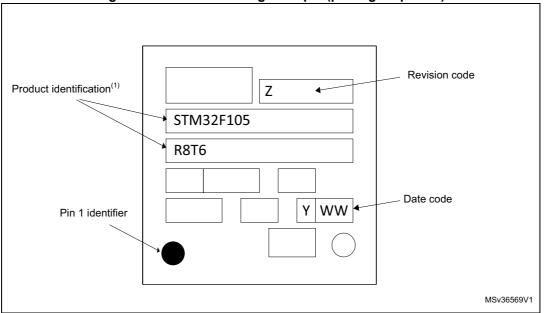


Figure 48.LQFP64 marking example (package top view)

 Parts marked as "ES", "E" or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering samples to run qualification activity.



Application	Crystal value in MHz (XT1)	PREDIV2	PLL2MUL	PLLSRC	PREDIV1	PLLMUL	USB prescaler (PLLVCO output)	PLL3MUL	l2Sn clock input	MCO (main clock output)
Ethernet only	25	/5	PLL2ON x8	PLL2	/5	PLLON x9	NA	PLL3ON x10	NA	XT1 (MII) PLL3 (RMII)
Ethernet + OTG	25	/5	PLL2ON x8	PLL2	/5	PLLON x9	/3	PLL3ON x10	NA	XT1 (MII) PLL3 (RMII)
Ethernet + OTG + basic audio	25	/5	PLL2ON x8	PLL2	/5	PLLON x9	/3	PLL3ON x10	PLL	XT1 (MII) PLL3 (RMII)
Ethernet + OTG + Audio class I ² S ⁽¹⁾	14.7456	/4	PLL2ON x12	PLL2	/4	PLLON x6.5	/3	PLL3ON x20	PLL3 VCO Out	NA ETH PHY must use its own crystal
OTG only	8	NA	PLL2OFF	XT1	/1	PLLON x9	/3	PLL3OFF	NA	NA
OTG + basic audio	8	NA	PLL2OFF	XT1	/1	PLLON x9	/3	PLL3OFF	PLL	NA
OTG + Audio class I ² S ⁽¹⁾	14.7456	/4	PLL2ON x12	PLL2	/4	PLLON x6.5	/3	PLL3ON x20	PLL3 VCO Out	NA
Audio class I ² S only ⁽¹⁾	14.7456	/4	PLL2ON x12	PLL2	/4	PLLON x6.5	NA	PLL3ON x20	PLL3 VCO out	NA

Table 63. PLL configurations

1. SYSCLK is set to be at 72 MHz except in this case where SYSCLK is at 71.88 MHz.

Table 64 give the I_{DD} run mode values that correspond to the conditions specified in *Table 63*.



Date	Revision	Changes
Date	Revision	Changes Document status promoted from Preliminary data to full datasheet. Number of DACs corrected in Table 3: STM32F105xx and STM32F107xx family versus STM32F103xx family. Note 5 added in Table 5: Pin definitions. V _{RERINT} and T _{Coeff} added to Table 12: Embedded internal reference voltage. Values added to Table 13: Maximum current consumption in Run mode, code with data processing running from Flash, Table 14: Maximum current consumption in Sleep mode, code running from Flash or RAM. Typical I _{DD_VBAT} value added in Table 16: Typical and maximum current consumptions in Slop and Standby modes. Figure 10: Typical current consumption on VBAT with RTC on vs. temperature at different VBAT values added. Values modified in Table 17: Typical current consumption in Run mode, code with data processing running from Flash and Table 18: Typical current consumption in Sleep mode, code running from Flash or RAM. f _{HSE_ext} min modified in Table 20: High-speed external user clock characteristics. CL1 and CL2 replaced by C in Table 22: HSE 3-25 MHz oscillator characteristics and Table 23: LSE oscillator characteristics (fLSE = 32.768 kHz), notes modified and moved below the tables. Note 1 modified below Figure 16: Typical application with an 8 MHz crystal. Conditions removed from Table 26: Low-power mode wakeup timings. Standards modified in Section 5.3.10: EMC characteristics. Grad Rep_ modified in Table 31: I/O static characteristics.

Table 65. Document revision history (continued)

